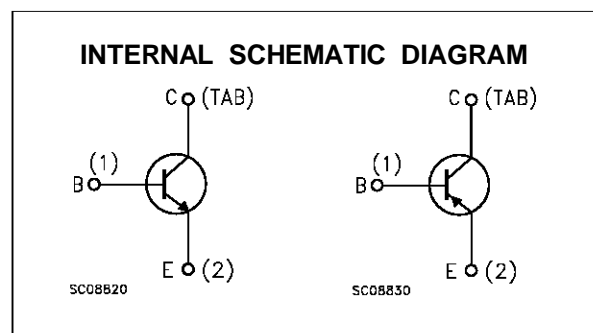
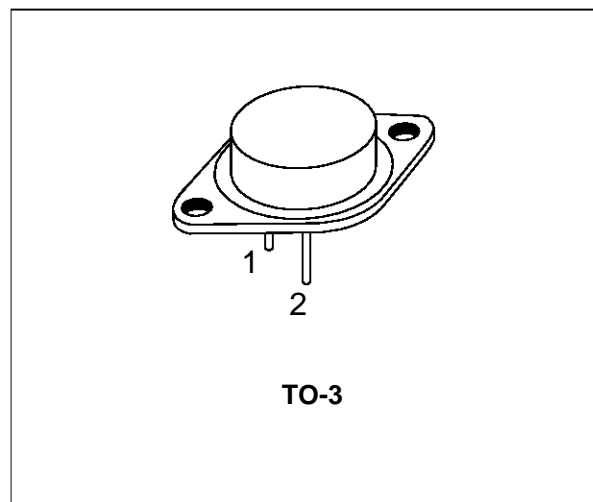


COMPLEMENTARY SILICON HIGH POWER TRANSISTORS

■ SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The MJ802 (NPN) and MJ4502 (PNP) are silicon epitaxial-base complementary power transistor in Jedec TO-3 metal case, intended for general purpose power amplifier and switching applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	90	V
V_{CBO}	Collector-base Voltage ($I_E = 0$)	100	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	4	V
I_C	Collector Current	30	A
I_B	Base Current	7.5	A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ\text{C}$	200	W
T_{stg}	Storage Temperature	-65 to 200	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	200	$^\circ\text{C}$

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	0.875	°C/W
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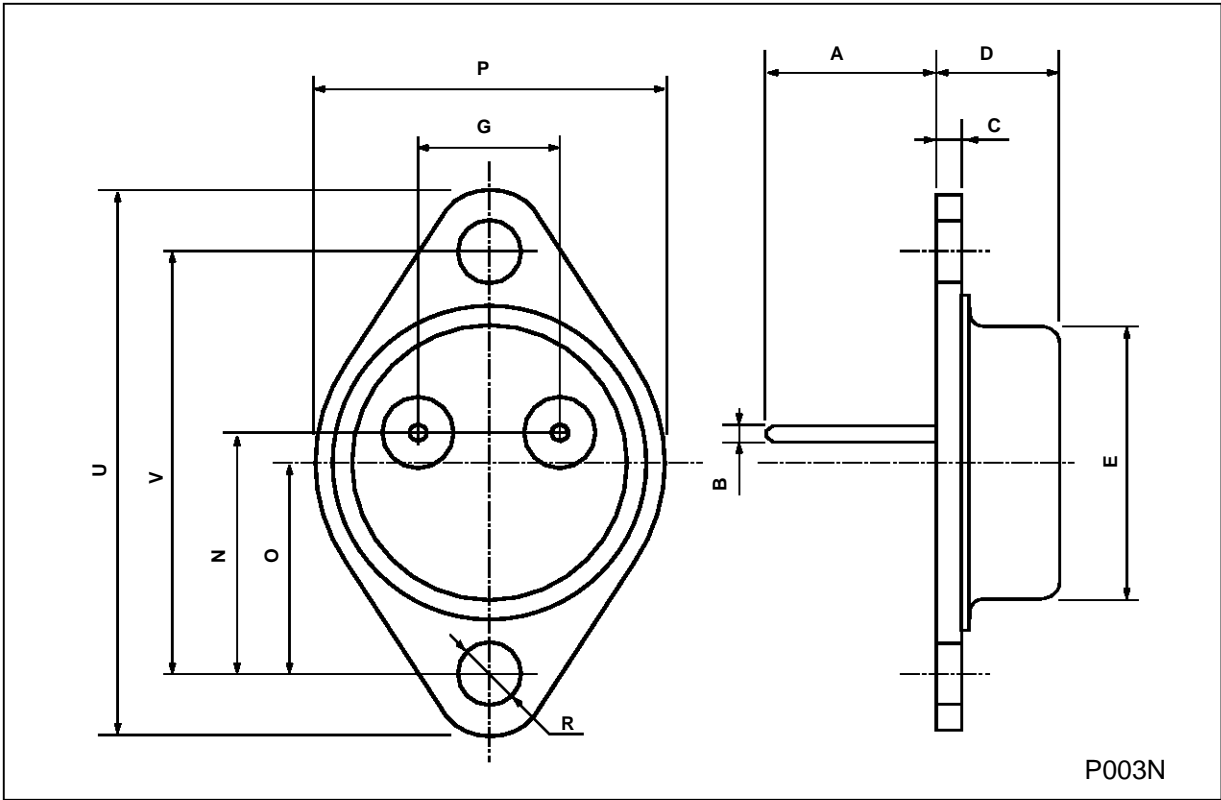
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 200 mA	90			V
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = 100 V T _{case} = 150 °C			1 5	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 4 V			1	mA
V _{CER(sus)} *	Collector-emitter Sustaining Voltage (R _{BE} = 100 Ω)	I _C = 200 mA	100			V
h _{FE} *	DC Current Gain	I _C = 7.5 A V _{CE} = 2 V	25		100	V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 7.5 A I _B = 0.75 A			0.8	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 7.5 A I _B = 0.75 A			1.3	V
V _{BE} *	Base-Emitter Voltage	I _C = 7.5 A V _{CE} = 2 V			1.3	V
f _T	Transition Frequency	I _C = 1 A V _{CE} = 10 V f = 1 MHz	2			MHz

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %
For PNP types voltage and current values are negative.

TO-3 (H) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A		11.7			0.460	
B	0.96		1.10	0.037		0.043
C			1.70			0.066
D			8.7			0.342
E			20.0			0.787
G		10.9			0.429	
N		16.9			0.665	
P			26.2			1.031
R	3.88		4.09	0.152		0.161
U			39.50			1.555
V		30.10			1.185	



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